

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 05-136417

(43)Date of publication of application : 01.06.1993

(51)Int.Cl.

H01L 29/784
H01L 27/12

(21)Application number : 04-108039

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(22)Date of filing : 27.04.1992

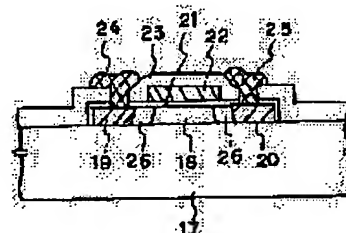
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(54) SEMICONDUCTOR DEVICE

(57)Abstract:

PURPOSE: To reduce leakage current in an OFF state of a thin film transistor.

CONSTITUTION: In a semiconductor device having a thin film transistor formed on a substrate, a semiconductor device where the thin film transistor consists of a thin polycrystalline film semiconductor 18 and has a low-doped region 26 adjacent to at least either the source region 19 or the drain region 20 of the thin film transistor and equal to this region in conductivity.



LEGAL STATUS

[Date of request for examination] 27.04.1992

[Date of sending the examiner's decision of rejection] 23.05.1995

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number] 2525707

[Date of registration] 31.05.1996

[Number of appeal against examiner's decision of rejection] 07-13125

[Date of requesting appeal against examiner's decision of rejection] 22.06.1995

[Date of extinction of right]